TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC7WH74FU, TC7WH74FK

D-TYPE FLIP FLOP WITH PRESET AND CLEAR

The TC7WH74 is an advanced high speed CMOS D-FLIP FLOP fabricated with silicon gate CMOS technology. It achieves the high speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation.

The signal level applied to the D INPUT is transferred to Q OUTPUT during the positive going transition of the CK pulse.

CLR and PR are independent of the CK and are accomplished by setting the appropriate input low. An input protection circuit ensures that 0 to 7V can be applied to the input pins without regard to the supply voltage. This device can be used to interface 5V to 3V system and two supply systems such as battery back up. This circuit prevents device destruction due to mismatched supply and input voltages.

FEATURES

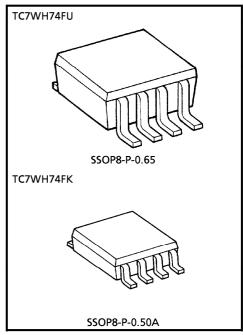
• High Speed $\cdots f_{MAX} = 170MHz$ (Typ.) at

 $V_{CC} = 5V$

• Low Power Dissipation $I_{CC} = 2\mu A$ (Max.) at

Ta = 25°C

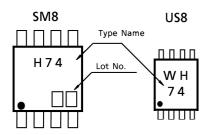
- High Noise Immunity ······· V_{NIH} = V_{NIL} = 28% V_{CC} (Min.)
- Power Down Protection is provided on all inputs.
- \bullet Balanced Propagation Delays …… $t_{\mbox{\scriptsize pLH}} {\mbox{\scriptsize \pm}} t_{\mbox{\scriptsize pHL}}$
- Wide Operation Voltage Range ··· V_{CC} (opr) = 2~5.5V



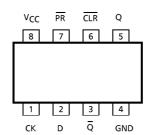
Weight

SSOP8-P-0.65 : 0.02g (Typ.) SSOP8-P-0.50A : 0.01g (Typ.)

MARKING



PIN ASSIGNMENT (TOP VIEW)



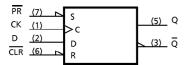
980508EBA2

TOSHIBA is continually working to improve the quality and the reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to observe standards of safety, and to avoid situations in which a malfunction or failure of a TOSHIBA product could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent products specifications. Also, please keep in mind the precautions and conditions set forth in the TOSHIBA Semiconductor Reliability Handbook.

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage Range	V _{CC}	-0.5~7.0	V
DC Input Voltage	VIN	-0.5~7.0	V
DC Output Voltage	Vout	-0.5~V _{CC} +0.5	\
Input Diode Current	lικ	– 20	mA
Output Diode Current	lok	± 20	mΑ
DC Output Current	lout	± 25	mA
DC V _{CC} /Ground Current	lcc	± 50	mΑ
Power Dissipation	D-	300 (SM8)	mW
Power Dissipation	PD	200 (US8)	IIIVV
Storage Temperature	T _{stg}	-65∼150	°C
Lead Temperature (10 s)	TL	260	°C

LOGIC DIAGRAM



TRUTH TABLE

	INP	UTS		OUTPUTS		FUNCTION
CLR	PR	D	СК	Q	Q	FUNCTION
L	Н	×	×	L	Н	CLEAR
Н	L	×	×	Н	L	PRESET
L	L	×	×	Н	Н	_
Н	Н	L	<u> </u>	L	Н	_
Н	Н	Н		Н	Ĺ	_
Н	Н	×	1	Qn	\overline{Q}_n	NO CHANGE

x : Don't care

RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	RATING	UNIT	
Supply Voltage	Vcc	2~5.5	V	
Input Voltage	VIN	0~V _{CC}	V	
Output Voltage	Vout	0~V _{CC}	V	
Operating Temperature	T _{opr}	- 40∼85	°C	
Input Rise and Fall Time	dt/dv	$0\sim100 \text{ (V}_{CC} = 3.3 \pm 0.3 \text{V)}$	ns/V	
Input Rise and Fall Time	at/dv	$0\sim20 \ (V_{CC} = 5 \pm 0.5V)$	115/V	

980508EBA2'

The products described in this document are subject to foreign exchange and foreign trade laws.
The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA CORPORATION for any infringements of intellectual property or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any intellectual property or other rights of TOSHIBA CORPORATION or others.
The information contained herein is subject to change without notice.

DC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	CVAADOL	(MAROL TEST COMPITION		Vcc	1	Γa = 25°0	2	Ta = -4	0~85°C	UNIT
CHARACTERISTIC SYMBO		. TEST CONDITION		Vcc (V)	MIN.	TYP.	MAX.	MIN.	MAX.	UNIT
High-Level				2.0	1.5		_	1.5	_	
Input Voltage	V _{IH}		_		V _{CC} × 0.7	1	_	V _{CC} × 0.7	1	V
Low-Level				2.0	_	1	0.5	_	0.5	
Input Voltage	VIL		_		_	_	V _C C × 0.3	_	V _C C × 0.3	V
		V _{IN} = V _{IH} or V _{IL}	I _{OH} = -50μA	2.0	1.9	2.0	_	1.9	_	V
High Loyal	V _{ОН}			3.0	2.9	3.0	_	2.9		
High-Level Output Voltage				4.5	4.4	4.5	_	4.4		
Output Voltage			$I_{OH} = -4mA$	3.0	2.58	1	_	2.48		
			$I_{OH} = -8mA$	4.5	3.94		_	3.80	1	
				2.0	_	0.0	0.1	_	0.1	V
Low-Level		$V_{IN} = V_{IH}$	$I_{OL} = 50 \mu A$	3.0	_	0.0	0.1	_	0.1	
Output Voltage	VOL	or V _{IL}		4.5	_	0.0	0.1	_	0.1	
Catput Voltage		0. 1	$I_{OL} = 4mA$	3.0	_	_	0.36	_	0.44	
			I _{OL} = 8mA	4.5	_	_	0.36	_	0.44	
Input Leakage Current	IIN	V _{IN} = V _{CC} or GND		0~ 5.5			± 0.1	_	± 1.0	μ A
Quiescent Supply Current	Icc	V _{IN} = V _{CC} or GND		5.5	_	_	2.0	_	20.0	μ A

TIMING REQUIREMENTS (Input $t_r = t_f = 3ns$)

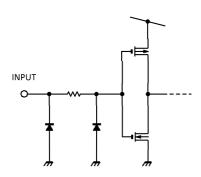
CHARACTERISTIC	SYMBOL TEST CONDITION I			Ta = 25°C		$Ta = -40 \sim 85^{\circ}C$	UNIT
CHARACTERISTIC STIVIBO		VCC VCC		TYP.	LIMIT	LIMIT	CIVIT
Minimum Pulse	t _W (L)		3.3 ± 0.3	_	6.0	7.0	nc
Width (CLOCK)	t _W (H)		5.0 ± 0.5	_	5.0	5.0	ns
Minimum Pulse	t _W (L)		3.3 ± 0.3	-	6.0	7.0	nc
Width (CLR, PR)	ι ₍ (ν) (μ)		5.0 ± 0.5	ı	5.0	5.0	ns
Minimum Set-up	+		3.3 ± 0.3	I	7.0	7.0	ns
Time	t _s		5.0 ± 0.5	_	5.0	5.0	113
Minimum Hold	+,		3.3 ± 0.3		0.5	0.5	ns
Time	th		5.0 ± 0.5	_	0.5	0.5	113
Minimum Removal	+		3.3 ± 0.3	_	5.0	5.0	ns
Time (CLR, PR)	^t rem		5.0 ± 0.5	_	3.0	3.0	113

AC ELECTRICAL	CHARACTERISTICS	(Input $t_r = t$	f = 3ns
----------------------	-----------------	------------------	---------

CHARACTERISTIC	CVMDOL	TEST C	TEST CONDITION		Ta = 25°C			Ta = -40~85°C		UNIT
CHARACTERISTIC	SYMBOL		V _{CC} (V)	C _L (pF)	MIN.	TYP.	MAX.	MIN.	MAX.	UNIT
Duana nation Dalas			3.3 ± 0.3	15	_	6.7	11.9	1.0	14.0	
Propagation Delay Time	t _{pLH}		3.3 ± 0.3	50	_	9.2	15.4	1.0	17.5	nc l
(CK-Q, \overline{Q})	tpHL		5.0 ± 0.5	15	_	4.6	7.3	1.0	8.5	ns
(CK-Q, Q)			3.0 ± 0.5	50	_	6.1	9.3	1.0	10.5	
		3.3 ± 0.3 - 5.0 ± 0.5 -	15	_	7.6	12.3	1.0	14.5		
Propagation Delay Time	t _{pLH}		3.3 ± 0.3	50		10.1	15.8	1.0	18.0	ns
$(\overline{CLR}, \overline{PR}-Q, \overline{Q})$			50+05	15	_	4.8	7.7	1.0	9.0	
(CLN, FN-Q, Q)			3.0 ± 0.3	50	_	6.3	9.7	1.0	11.0	
		3.3 ± 0.3	15	80	125	_	70	_		
Maximum Clock	f		3.3 ± 0.3	50	50	75	_	45	_	MHz
Frequency	fMAX		5.0 ± 0.5	15	130	170	_	110	_	IVITZ
		5.0 ± 0.	3.0 ± 0.3	50	90	115	_	75	_	
Input Capacitance	C _{IN}			_	_	4	10	_	10	pF
Power Dissipation Capacitance	C _{PD}	(Note 1)				22	_	_	_	pF

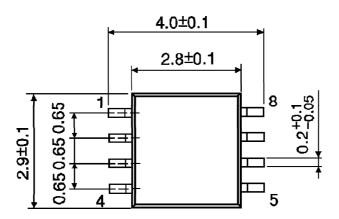
(Note 1): C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $|CC| = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$

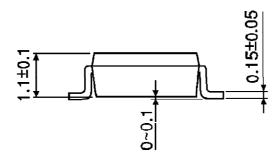
INPUT EQUIVALENT CIRCUIT



OUTLINE DRAWING SSOP8-P-0.65

Unit: mm

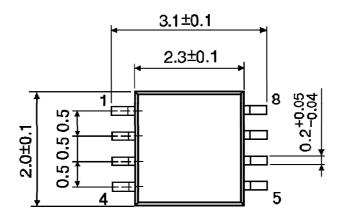


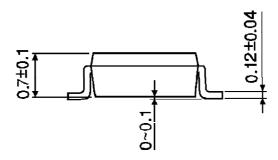


Weight: 0.02g (Typ.)

OUTLINE DRAWING SSOP8-P-0.50A

Unit: mm





Weight: 0.01g (Typ.)